

L Number	Hits	Search Text	DB	Time stamp
2	1624	(((((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)) and (float\$3 near5 gate)) and (source drain)) and ("ONO" (oxide near5 nitride near5 oxide))) and spacer	USPAT; US-PGPUB	2004/06/14 06:17
3	1423	(((((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)) and (float\$3 near5 gate)) and (source drain)) and ("ONO" (oxide near5 nitride near5 oxide))) and spacer) and (trench recess groove hole open\$3)	USPAT; US-PGPUB	2004/06/14 06:18
4	1404	(((((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)) and (float\$3 near5 gate)) and (source drain)) and ("ONO" (oxide near5 nitride near5 oxide))) and spacer) and (trench recess groove hole open\$3)) and (source and drain)	USPAT; US-PGPUB	2004/06/14 05:57
5	1218	(((((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)) and (float\$3 near5 gate)) and (source drain)) and ("ONO" (oxide near5 nitride near5 oxide))) and spacer) and (trench recess groove hole open\$3)) and (source and drain)) and ((source and drain) same ((select control) near5 gate))	USPAT; US-PGPUB	2004/06/14 05:59
6	17	(((((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)) and (float\$3 near5 gate)) and (source drain)) and ("ONO" (oxide near5 nitride near5 oxide))) and spacer	EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:18
7	13	(((((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)) and (float\$3 near5 gate)) and (source drain)) and ("ONO" (oxide near5 nitride near5 oxide))) and spacer) and (trench recess groove hole open\$3)	EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:18